

### REMARKS

The Final Office Action mailed January 11, 2005 has been received and carefully noted. The following remarks are submitted as a full and complete response thereto.

No extension of time is believed to be required based upon the filing of this Amendment prior to the deadline of the three-month statutory period (i.e., April 11, 2005). Authorization is granted to charge counsel's Deposit Account No. 01-2300, referencing **Attorney Docket No. 103213-00065**, for any additional fees necessary for entry of this Amendment.

Claims 4-7 have been amended and claims 1-3 have been canceled. Applicants submit that the amendments made herein are fully supported in the Specification and the drawings, as originally filed, and therefore no new matter has been introduced. Accordingly, claims 4-7 are pending in the present application and are respectfully submitted for reconsideration.

Claims 1-3 and 5-6 were finally rejected under 35 U.S.C. § 102(c) as being anticipated by the Cheng et al. patent (U.S. Patent No. 6,576,934). In addition, dependent claims 4 and 7 were finally rejected under 35 U.S.C. § 103(a) as being unpatentable over the Cheng et al. patent. Claims 1-3 have been canceled, thus the rejections with respect to these claims are now moot. Claims 4-6 have been rewritten in independent form including all of the limitations of claims 2-3 and claim 7 has been amended to depend from claim 4. The rejections are respectfully traversed and reconsideration is requested.

Independent claim 4, as amended, recites a semiconductor integrated circuit device, comprising an output circuit, wherein the output circuit comprises an open-drain N-channel MOSFET; and an output terminal connected to a drain of the open-drain N-channel MOSFET, wherein the open-drain N-channel MOSFET comprises a drain region formed of an N-type

semiconductor layer; a P-type impurity diffusion layer formed within the drain region; two high-concentration N-type impurity diffusion layers formed within the drain region so as to sandwich the P-type impurity diffusion layer; a low-concentration N-type impurity diffusion region formed in contact with the drain region; and a drain electrode connected to the P-type impurity diffusion layer and to the two high-concentration N-type impurity diffusion layers, wherein there are provided a plurality of the output circuit, wherein a peripheral portion of the drain region of the open-drain N-channel MOSFET and a peripheral portion of a source region of the open-drain N-channel MOSFET each have, as seen in a plan view, a substantially circular shape or a substantially regular-polygonal shape with four or more sides, and gates of the open-drain N-channel MOSFET are formed in a net-like pattern.

In addition, independent claim 5, as amended, recites a similar semiconductor integrated circuit device, wherein the drain region and a source region of the open-drain N-channel MOSFET are formed in a pattern like teeth of a comb. Further, independent claim 6, as amended, recites a similar semiconductor integrated circuit device, wherein a peripheral portion of the drain region of the open-drain N-channel MOSFET and a peripheral portion of a source region of the open-drain N-channel MOSFET have, as seen in a plan view, different shapes.

Applicants respectfully submit that the semiconductor integrated circuit, as claimed in the present invention, is neither disclosed nor suggested by the Cheng et al. patent. Specifically, the semiconductor integrated circuit device recited in the present invention adopt, as the structure of a MOSFET for an open drain circuit, a structure involving a drain, gate and source so shaped as described in paragraph [0021] of the Specification and shown in Fig. 3B. This makes it possible to realize a MOSFET for an open drain circuit which offers high area use efficiency combined with a high withstand voltage. In contrast, the Cheng et al. patent discloses nothing about the

shapes of the drain, source and gate of a MOSFET, and thus does not aim at enhanced area use efficiency. Further, no support has been provided to show that such design choices would have been obvious at the time of the invention.

Since the Cheng et al. patent fails to disclose or suggest anything comparable with the specific shapes of the drain, source and gate of a MOSFET for an open drain circuit, as claimed in the present invention, Applicants respectfully submit that the semiconductor integrated circuit device as claimed in the present invention is not anticipated or unpatentable over the Cheng et al. patent.

It is further submitted that claim 7 is also patentable and in condition for allowance due to its dependency upon independent claim 4, since the dependent claim differs in scope from the parent claim. Dependent claim 7 depends from independent claim 4, and thus is further limited to additional features of the invention. Therefore, it is respectfully submitted that the dependent claim is patentable over the Cheng et al. patent for at least the reasons set forth above with respect to independent claim 4. Reconsideration is requested.

Entry of this Amendment after final rejection is therefore submitted as proper in that it places the application in condition for allowance. Particularly, the present Amendment is submitted as not raising new issues or requiring further consideration or searching. Undersigned counsel would accordingly appreciate the Examiner telephoning counsel prior to the expiration of the six-month statutory period (i.e., July 11, 2005) to indicate the disposition of this Response.

If for any reason the Examiner determines that the application is not now in condition for allowance, it is respectfully requested that the Examiner contact the Applicant's undersigned counsel at the telephone number, indicated below, to arrange for an interview to expedite the disposition of this application.

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Respectfully submitted,



Marylee Jenkins  
Registration No. 37,645  
Attorney for Applicants

Customer No. 004372  
ARENT FOX, PLLC  
1675 Broadway  
New York, New York 10019  
Tel: (212) 484-3928  
Fax: (212) 484-3990